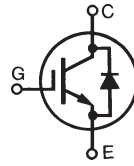




XPT™ 600V IGBT GenX3™ w/ Diode

IXXH50N60B3D1

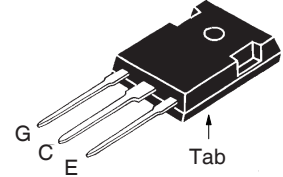
Extreme Light Punch Through
IGBT for 5-30kHz Switching



$$\begin{aligned} V_{CES} &= 600V \\ I_{C110} &= 50A \\ V_{CE(sat)} &\leq 1.80V \\ t_{fi(typ)} &= 135ns \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 175^\circ\text{C}$	600	V
V_{CGR}	$T_J = 25^\circ\text{C to } 175^\circ\text{C}, R_{GE} = 1M\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C (Chip Capability)}$	120	A
I_{C110}	$T_C = 110^\circ\text{C}$	50	A
I_{F110}	$T_C = 110^\circ\text{C}$	30	A
I_{CM}	$T_C = 25^\circ\text{C}, 1\text{ms}$	200	A
I_A	$T_C = 25^\circ\text{C}$	25	A
E_{AS}	$T_C = 25^\circ\text{C}$	200	mJ
SSOA (RBSOA)	$V_{GE} = 15V, T_{VJ} = 150^\circ\text{C}, R_G = 5\Omega$ Clamped Inductive Load	$I_{CM} = 100$ $@ V_{CE} \leq V_{CES}$	A
t_{sc} (SCSOA)	$V_{GE} = 15V, V_{CE} = 360V, T_J = 150^\circ\text{C}$ $R_G = 22\Omega$, Non Repetitive	10	μs
P_C	$T_C = 25^\circ\text{C}$	600	W
T_J		-55 ... +175	$^\circ\text{C}$
T_{JM}		175	$^\circ\text{C}$
T_{stg}		-55 ... +175	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ\text{C}$
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	$^\circ\text{C}$
M_d	Mounting Torque	1.13/10	Nm/lb.in.
Weight		6	g

TO-247



G = Gate C = Collector
E = Emitter Tab = Collector

Features

- Optimized for 5-30kHz Switching
- Square RBSOA
- Anti-Parallel Ultra Fast Diode
- Avalanche Capability
- Short Circuit Capability
- International Standard Package

Advantages

- High Power Density
- 175°C Rated
- Extremely Rugged
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu\text{A}, V_{GE} = 0V$	600		V
$V_{GE(th)}$	$I_C = 250\mu\text{A}, V_{CE} = V_{GE}$	3.5		6.0 V
I_{CES}	$V_{CE} = V_{CES}, V_{GE} = 0V$ $T_J = 150^\circ\text{C}$			25 μA 3 mA
I_{GES}	$V_{CE} = 0V, V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 36A, V_{GE} = 15V$, Note 1 $T_J = 150^\circ\text{C}$		1.55 1.80	V V

Symbol Test Conditions

(T_J = 25°C Unless Otherwise Specified)

Characteristic Values

Min. Typ. Max.

g_{fs}	I _C = 36A, V _{CE} = 10V, Note 1	12	19	S
C_{ies}	V _{CE} = 25V, V _{GE} = 0V, f = 1MHz		2230	pF
C_{oes}			195	pF
C_{res}			44	pF
Q_{g(on)}	I _C = 36A, V _{GE} = 15V, V _{CE} = 0.5 • V _{CES}		70	nC
Q_{ge}			16	nC
Q_{gc}			29	nC
t_{d(on)}	Inductive load, T_J = 25°C I _C = 36A, V _{GE} = 15V V _{CE} = 360V, R _G = 5Ω Note 2		27	ns
t_{ri}			40	ns
E_{on}			0.67	mJ
t_{d(off)}			100	ns
t_{fi}			135	ns
E_{off}			0.74	mJ
t_{d(on)}	Inductive load, T_J = 150°C I _C = 36A, V _{GE} = 15V V _{CE} = 360V, R _G = 5Ω Note 2		30	ns
t_{ri}			45	ns
E_{on}			1.40	mJ
t_{d(off)}			130	ns
t_{fi}			190	ns
E_{off}			1.20	mJ
R_{thJC}			0.25	°C/W
R_{thCS}		0.21		°C/W

Reverse Diode (FRED)

Symbol Test Conditions

(T_J = 25°C Unless Otherwise Specified)

Characteristic Values

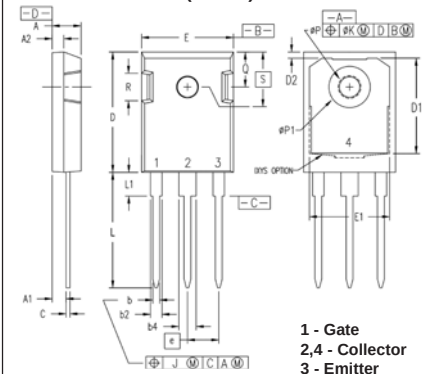
Min. Typ. Max.

V_F	I _F = 30A, V _{GE} = 0V, Note 1	T _J = 150°C	1.6	2.7 V
I_{RM}	I _F = 30A, V _{GE} = 0V, -di _F /dt = 100A/μs, V _R = 100V		100	4 A
t_{rr}	I _F = 1A, V _{GE} = 0V, -di _F /dt = 100A/μs, V _R = 30V	T _J = 100°C	25	ns
R_{thJC}				0.9 °C/W

Notes:

1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.
2. Switching times & energy losses may increase for higher V_{CE}(clamp), T_J or R_G.

TO-247 (IXXH) Outline



Dim.	Millimeter		Inches	
	min	max	min	max
A	4.70	5.30	0.185	0.209
A1	2.21	2.59	0.087	0.102
A2	1.50	2.49	0.059	0.098
b	0.99	1.40	0.039	0.055
b2	1.65	2.39	0.065	0.094
b4	2.59	3.43	0.102	0.135
c	0.38	0.89	0.015	0.035
D	20.79	21.45	0.819	0.845
D1	13.07	-	0.515	-
D2	0.51	1.35	0.020	0.053
E	15.48	16.24	0.610	0.640
E1	13.45	-	0.53	-
E2	4.31	5.48	0.170	0.216
e	5.45 BSC		0.215 BSC	
L	19.80	20.30	0.078	0.800
L1	-	4.49	-	0.177
Ø P	3.55	3.65	0.140	0.144
Ø P1	-	7.39	-	0.290
Q	5.38	6.19	0.212	0.244
S	6.14 BSC		0.242 BSC	

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

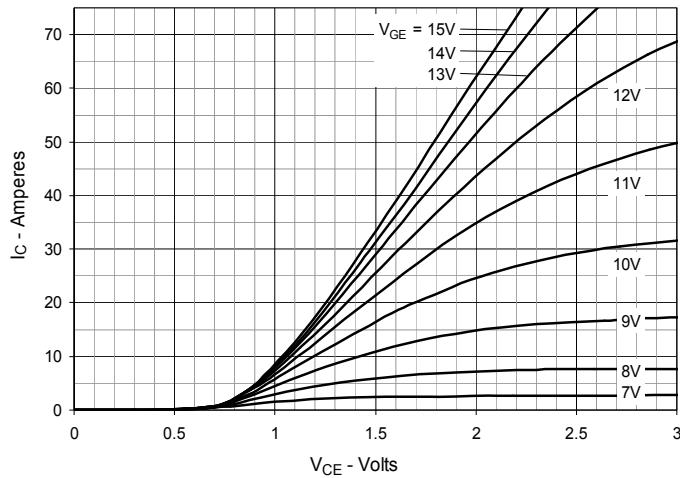
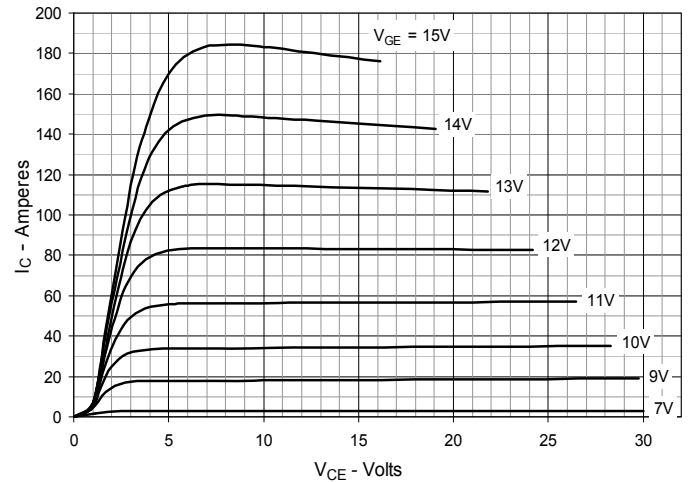
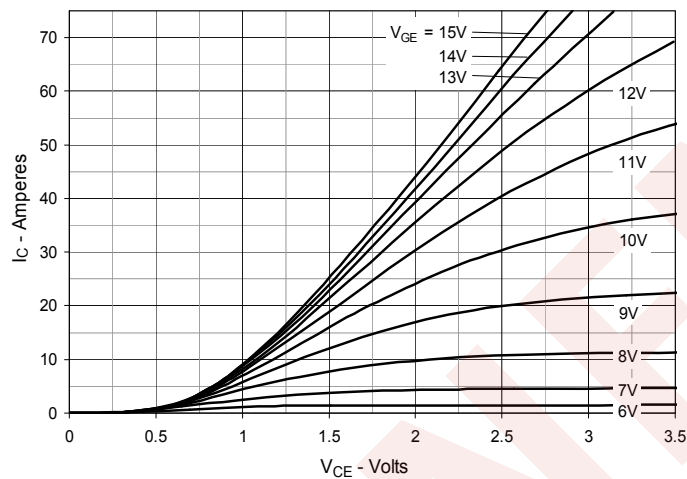
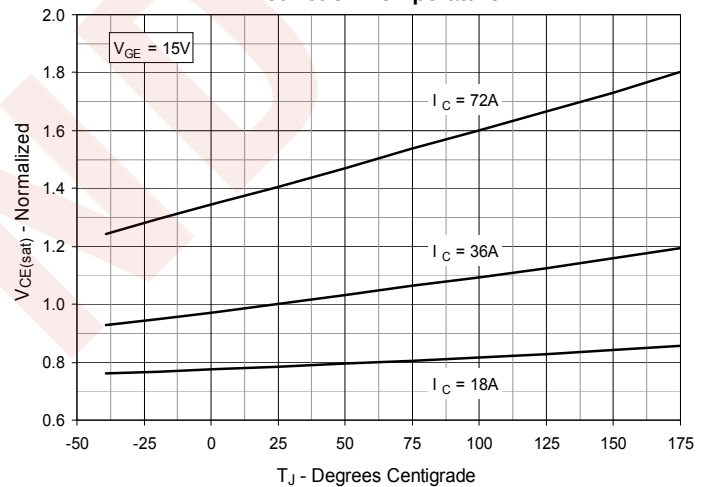
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$ Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$ Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$ Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

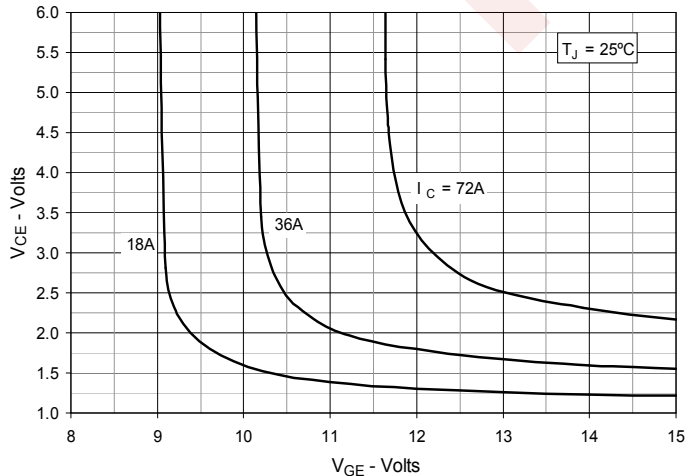


Fig. 6. Input Admittance

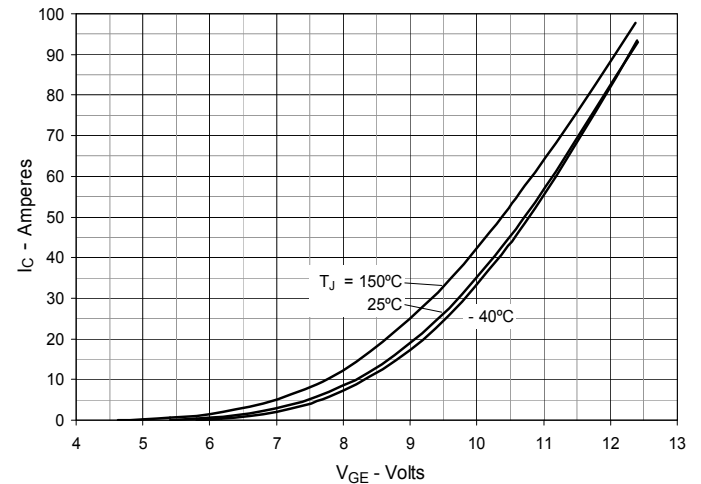


Fig. 7. Transconductance

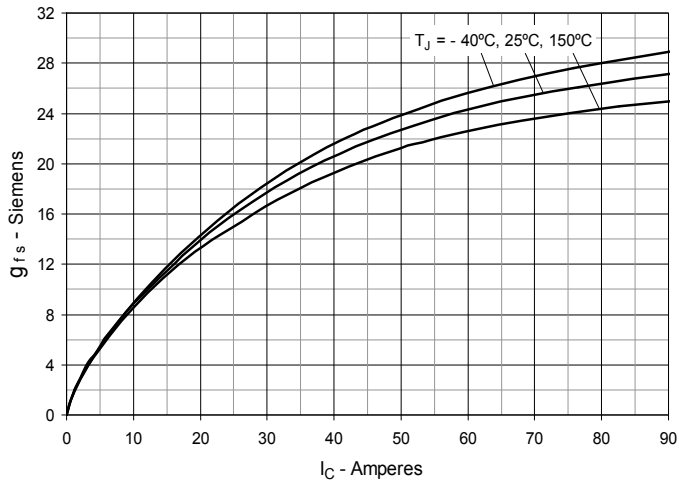


Fig. 8. Gate Charge

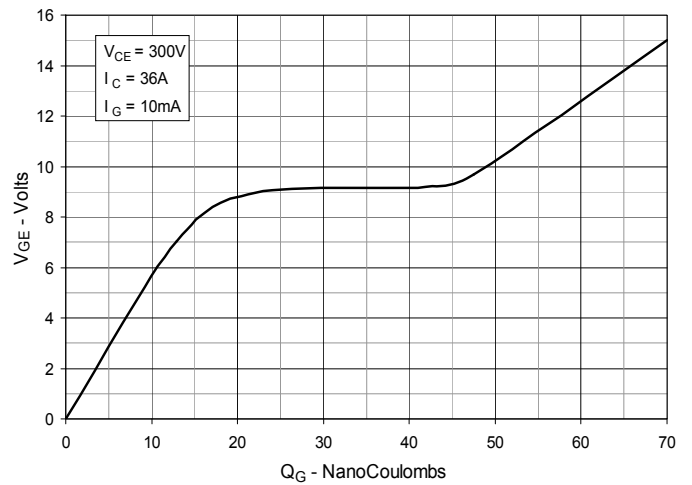


Fig. 9. Capacitance

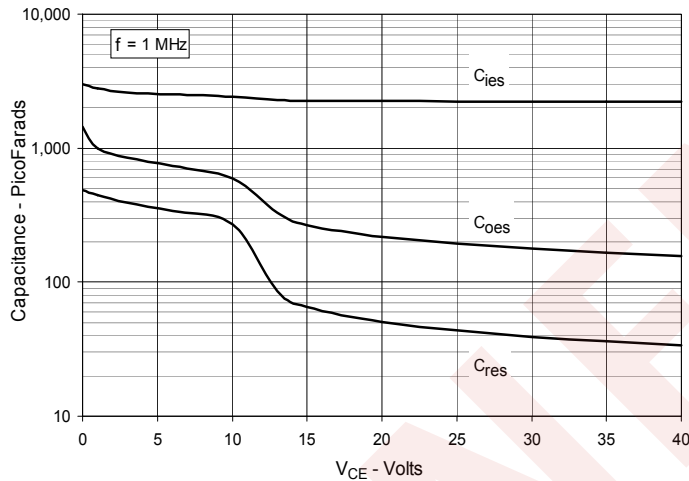


Fig. 10. Reverse-Bias Safe Operating Area

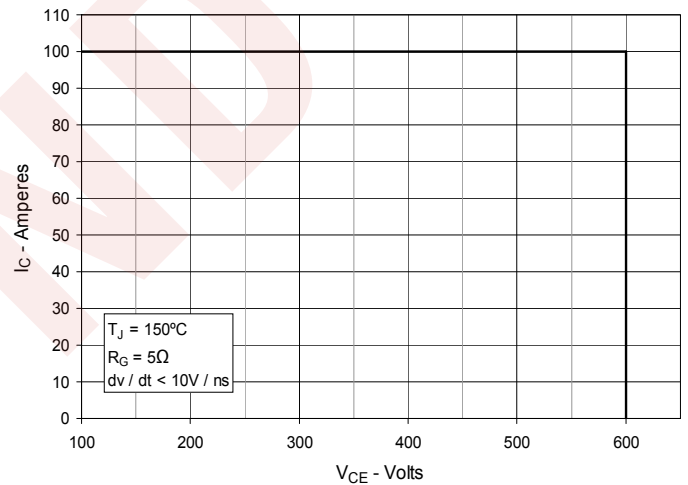


Fig. 11. Forward-Bias Safe Operating Area

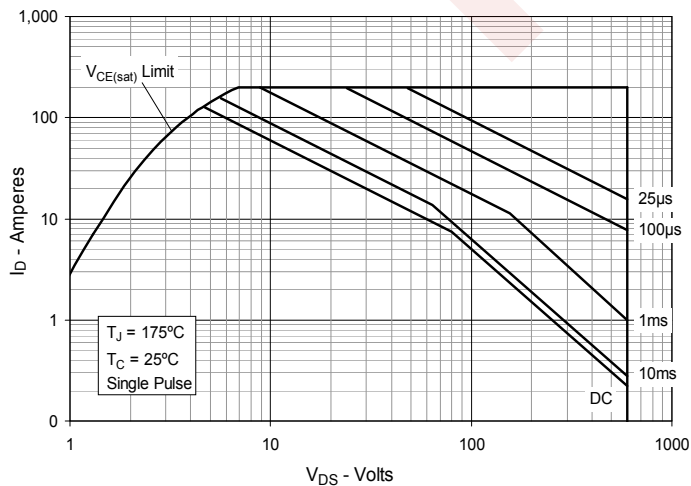


Fig. 12. Maximum Transient Thermal Impedance

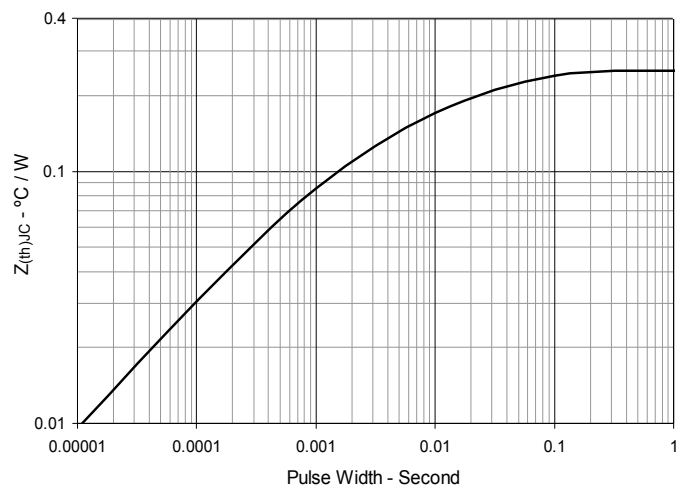


Fig. 13. Inductive Switching Energy Loss vs. Gate Resistance

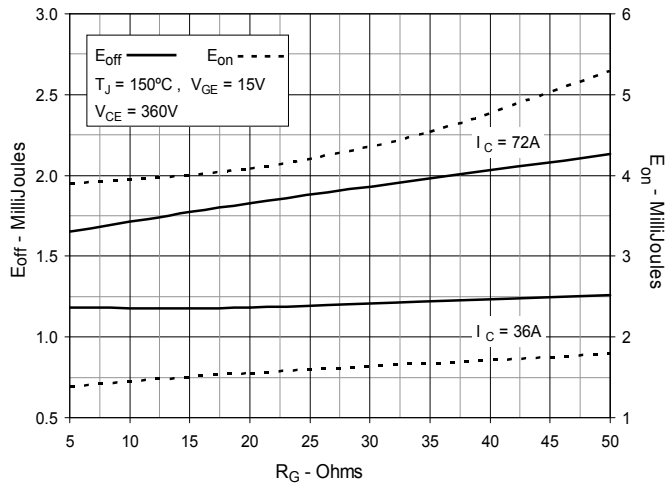


Fig. 14. Inductive Switching Energy Loss vs. Collector Current

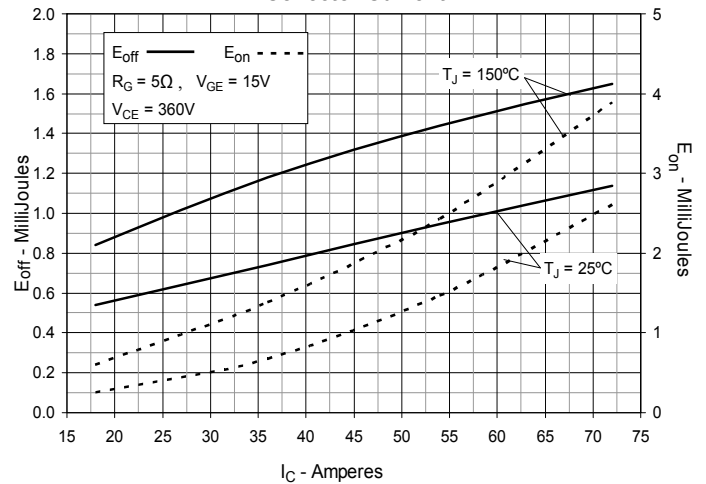


Fig. 15. Inductive Switching Energy Loss vs. Junction Temperature

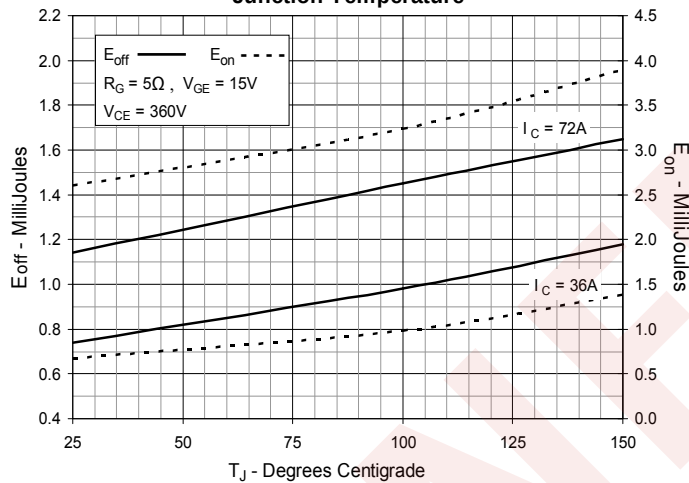


Fig. 16. Inductive Turn-off Switching Times vs. Gate Resistance

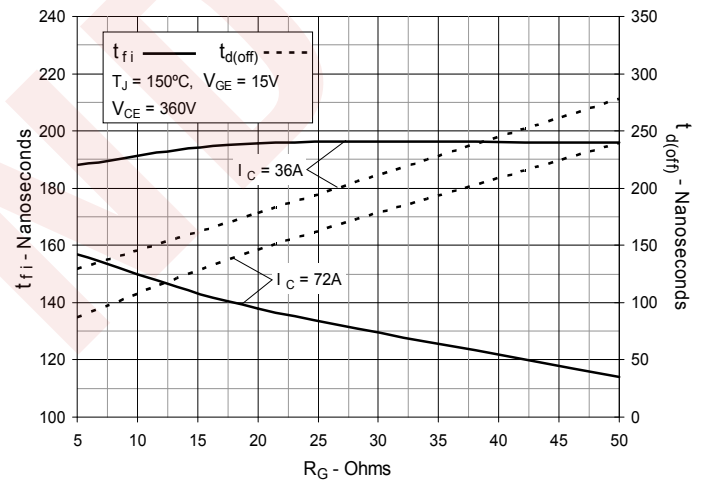


Fig. 17. Inductive Turn-off Switching Times vs. Collector Current

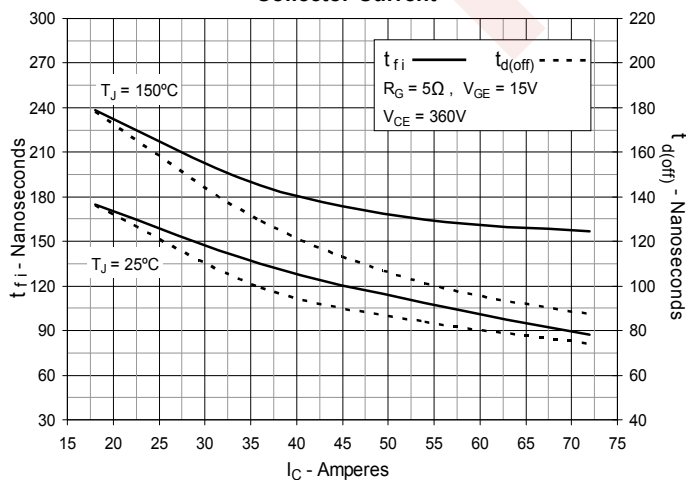


Fig. 18. Inductive Turn-off Switching Times vs. Junction Temperature

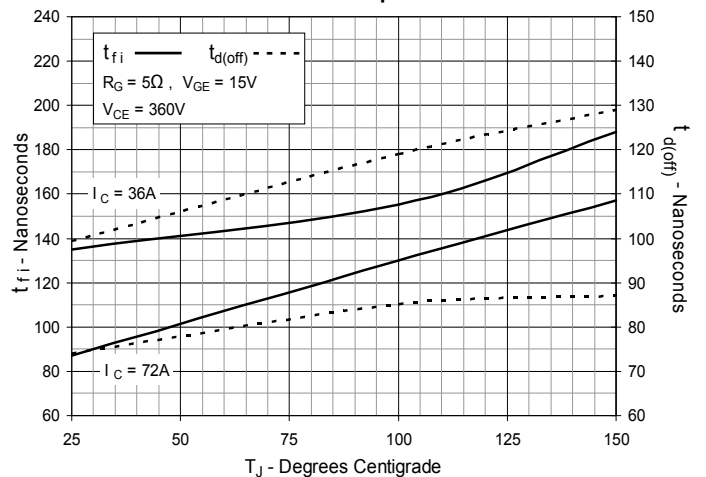


Fig. 19. Inductive Turn-on Switching Times vs. Gate Resistance

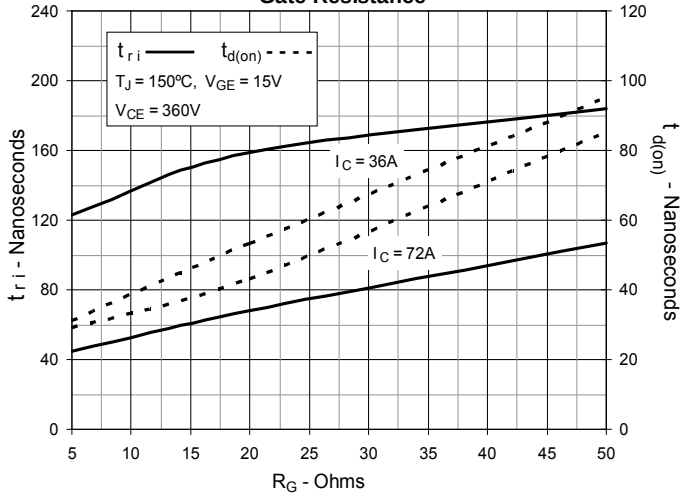


Fig. 20. Inductive Turn-on Switching Times vs. Collector Current

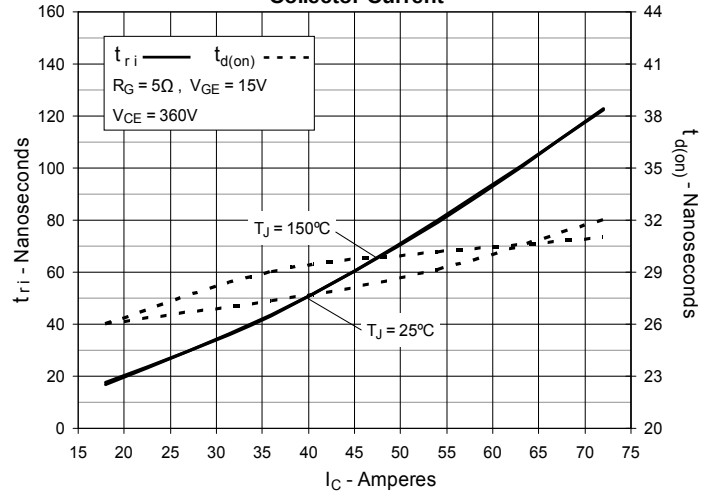
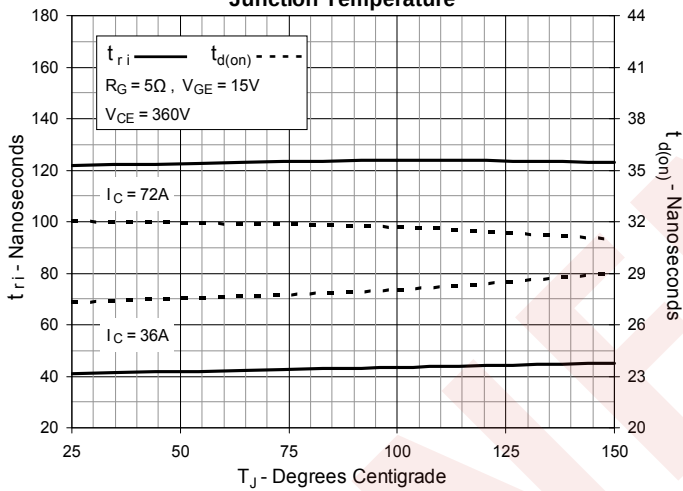


Fig. 21. Inductive Turn-on Switching Times vs. Junction Temperature



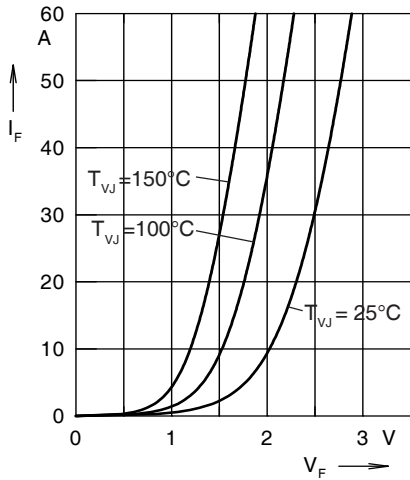
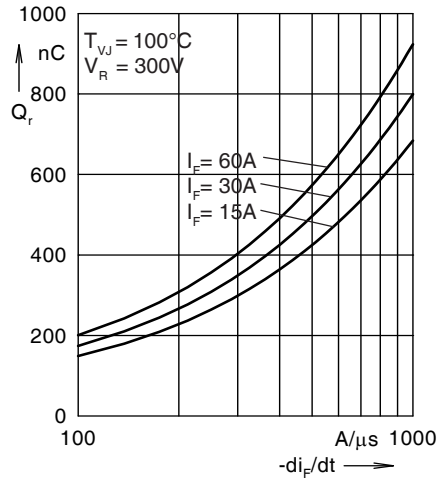
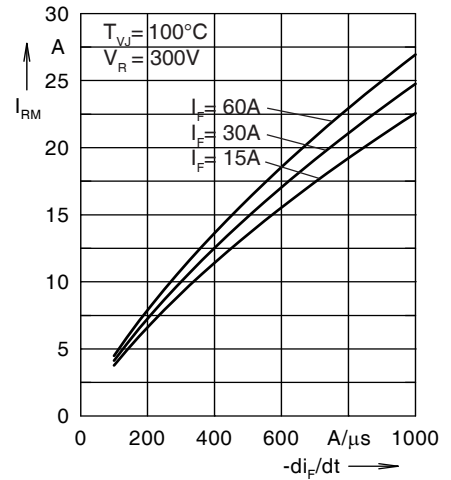
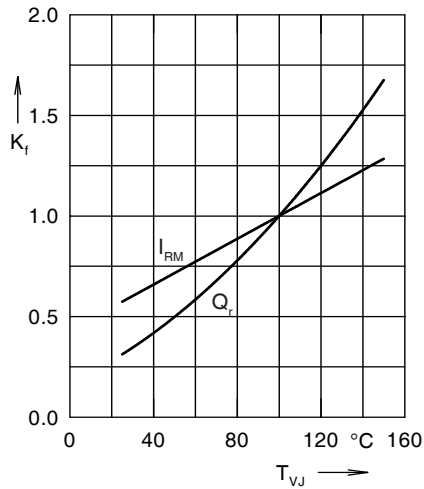
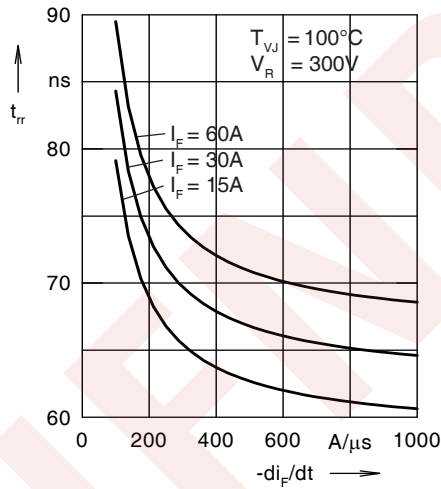
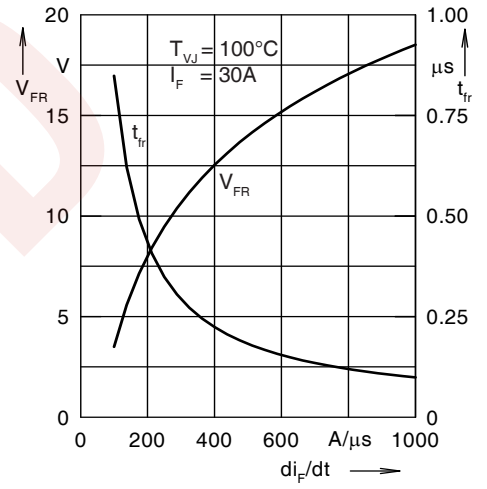
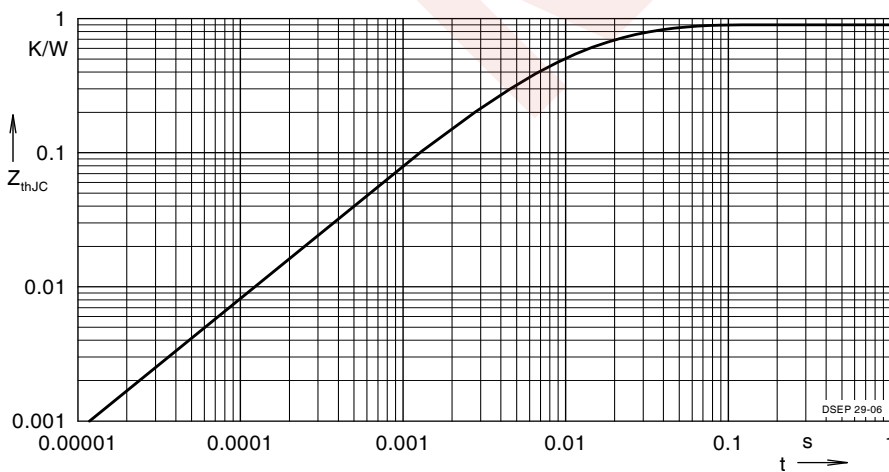
Fig. 22. Forward Current I_F Versus V_F Fig. 23. Reverse Recovery Charge Q_r Versus $-di_F/dt$ Fig. 24. Peak Reverse Current I_{RM} Versus $-di_F/dt$ Fig. 25. Dynamic Parameters Q_r , I_{RM} Versus T_{VJ} Fig. 26. Recovery Time t_{rr} Versus $-di_F/dt$ Fig. 27. Peak Forward Voltage V_{FR} and t_{fr} Versus di_F/dt 

Fig. 28. Transient Thermal Resistance Junction to Case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.502	0.0052
2	0.193	0.0003
3	0.205	0.0162

NOT FOR NEW DESIGN

NEW



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